

ABSTRACT OF THE DISCLOSURE

Semiconductor devices and methods of forming devices that have field oxides in trenches are disclosed. According to the methods, a semiconductor substrate is prepared. An upper trench is formed at a predetermined region of the semiconductor substrate and a bottom trench is formed at a bottom surface of the upper trench. A field oxide is formed to fill the bottom trench and the upper trench. At this time, the upper trench has a wider width than the bottom trench.